



NTE2684

Silicon NPN Transistor

High Current Switch

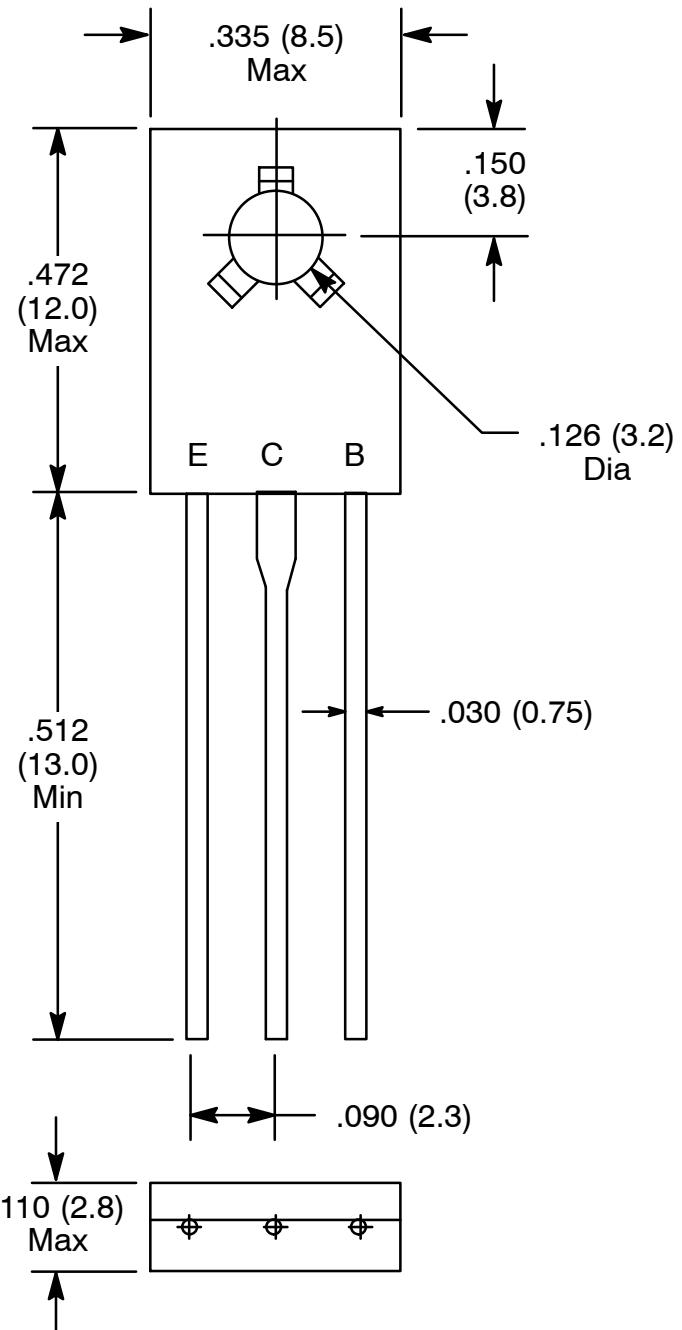
TO126 Type Package

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage (Open Emitter), V_{CBO}	120V
Collector–Emitter Voltage (Open Base), V_{EBO}	75V
Emitter–Base Voltage (Open Collector), V_{EBO}	5V
DC Collector Current, I_C	5A
Peak Collector Current, I_{CM}	10A
Peak Base Current, I_{BM}	2A
Total Power Dissipation ($T_C \leq +75^\circ\text{C}$), P_T	15W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-65° to +150°C
Thermal Resistance, Junction-to-Ambient, R_{thJA}	100K/W
Thermal Resistance, Junction-to-Case, R_{thJC}	5K/W

Electrical Characteristic: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Collector–Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 5\text{A}$, $I_B = 0.5\text{A}$		–	–	0.9	V
		$I_C = 7\text{A}$, $I_B = 0.7\text{A}$		–	–	1.2	V
Base–Emitter Saturation Voltage	$V_{BE(\text{sat})}$	$I_C = 5\text{A}$, $I_B = 0.5\text{A}$		–	–	1.7	V
		$I_C = 7\text{A}$, $I_B = 0.7\text{A}$		–	–	2.0	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 100\text{V}$, $I_E = 0$		–	–	0.1	$\leq\text{A}$
			$T_J = +100^\circ\text{C}$	–	–	10	$\leq\text{A}$
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$		–	–	0.1	$\leq\text{A}$
DC Current Gain	h_{FE}	$I_C = 0.5\text{A}$, $V_{CE} = 10\text{V}$		45	–	450	
Collector Capacitance	C_C	$I_E = 0$, $V_{CB} = 10\text{V}$, $f = 1\text{MHz}$		–	40	–	pF
Transition Frequency	f_T	$I_C = 0.5\text{A}$, $V_{CE} = 5\text{V}$, $f = 100\text{MHz}$		–	100	–	MHz
Turn-On Time	t_{on}	$I_{Con} = 1\text{A}$, $I_{Bon} = -I_{Boff} = 0.1\text{A}$		–	60	100	ns
		$I_{Con} = 2\text{A}$, $I_{Bon} = -I_{Boff} = 0.2\text{A}$		–	–	80	ns
		$I_{Con} = 5\text{A}$, $I_{Bon} = -I_{Boff} = 0.5\text{A}$		–	180	300	ns
Turn-Off Time	t_{off}	$I_{Con} = 1\text{A}$, $I_{Bon} = -I_{Boff} = 0.1\text{A}$		–	600	800	ns
		$I_{Con} = 2\text{A}$, $I_{Bon} = -I_{Boff} = 0.2\text{A}$		–	450	700	ns
		$I_{Con} = 5\text{A}$, $I_{Bon} = -I_{Boff} = 0.5\text{A}$		–	350	500	ns



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by NTE manufacturer:

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#)
[2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)